
UNIVERSITI SAINS MALAYSIA

Semester II Examination
Academic Session 2007/2008

April 2008

EEE 510 – ANALOG CIRCUIT DESIGN

Time : 3 hours

INSTRUCTION TO CANDIDATE:

Please ensure that this examination paper contains **SIX (6)** printed pages and **SIX (6)** questions before answering.

Answer **FIVE (5)** questions.

Distribution of marks for each question is given accordingly.

All questions must be answered in English.

- Given a MOS transistor in a configuration as shown in Figure 1. Draw the small signal model of the transistor. Assume $V_{sb} = V_{ds} = 0$. g_{mb} , r_o , C_{sb} and C_{db} are ignored. Prove that

$$f_T = \frac{1}{2\pi} \frac{g_m}{C_{gs} + C_{gb} + C_{gd}}$$

Compare the above expression with the unity gain frequency expression for the BJT.

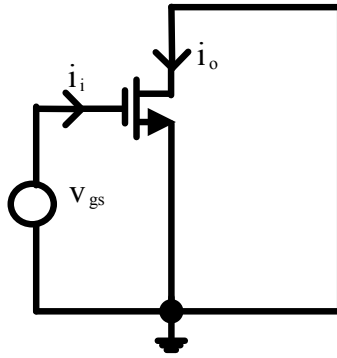


Figure 1

(20 marks)

- Determine the voltage gain of the transistor amplifier circuit shown in Figure 2. Assume $\beta_{ac} = \beta_{dc} = 100$. $V_T = 26 \text{ mV}$ and $V_{BE} = 0.7 \text{ V}$. Neglect all parasitic elements in the small-signal equivalent circuit of the BJT in this amplifier circuit. Neglect the base charging capacitance and the collector-base resistances. Assume that r_o is very large.

(20 marks)

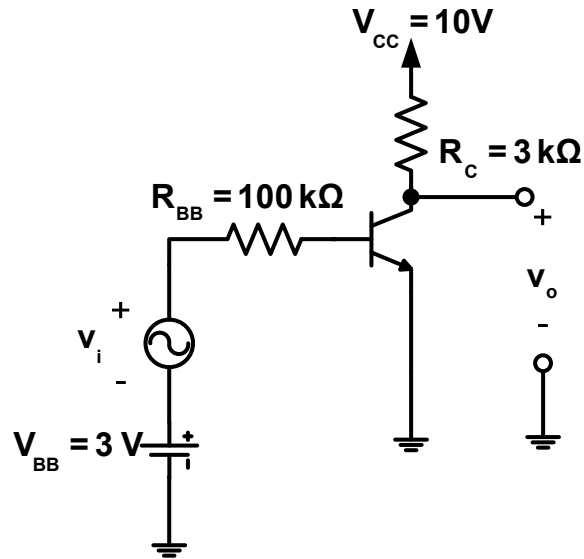


Figure 2

3. Consider the BiCMOS amplifier shown in Figure 3. The BJT has $V_{BE} = 0.7\text{ V}$ and $\beta = 200$. The NMOS transistor has a threshold voltage $V_t = 1\text{ V}$ and $k' W/L = 2\text{ mA/V}^2$. Consider the DC bias circuit for this amplifier. Neglect the base current of Q_2 in determining the current in Q_1 . Find the DC bias currents in Q_1 and Q_2 , and show that they are approximately $100\text{ }\mu\text{A}$ and 1 mA respectively.

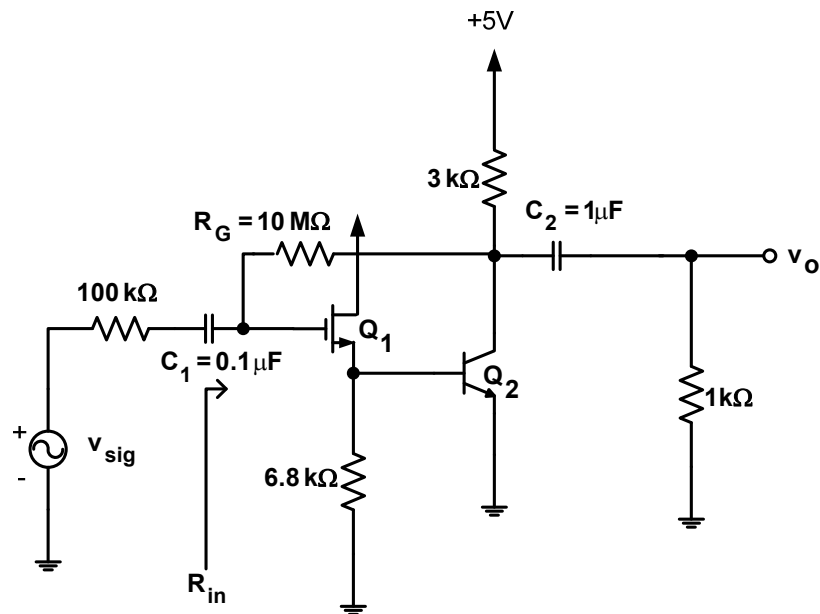


Figure 3

(20 marks)

4. Figure 4 shows a non-inverting configuration of an operational amplifier.

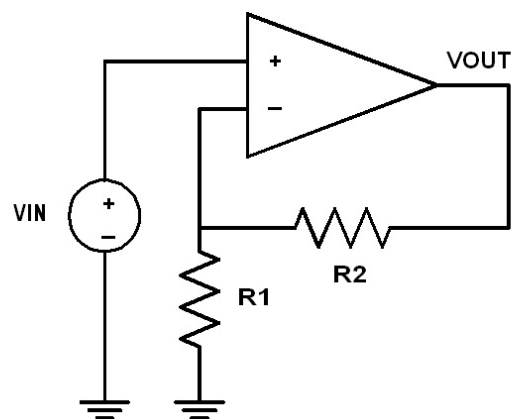


Figure 4

- (a) Identify the type of feedback in this circuit. (5 marks)
- (b) Find the expression of the loop gain. (5 marks)
- (c) Find the expression of the closed loop gain. (10 marks)

5. Circuit in Figure 5 has a GBW of 200 MHz. If VDD is 2.5 V and

$$\mu_n C_{OX} = 100 \mu \frac{A}{V^2}, \mu_p C_{OX} = 50 \mu \frac{A}{V^2}, V_{thn} = |V_{thp}| = 0.5V \text{ and CL is } 1 \text{ pF}$$

Find :

- (a) gm. (10 marks)
- (b) W/L of MN1 (10 marks)

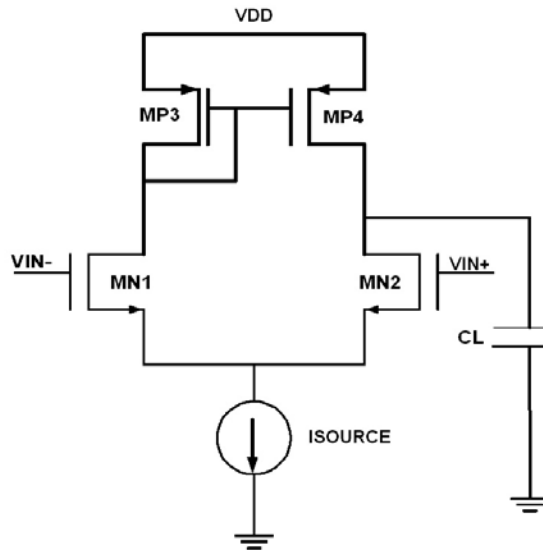


Figure 5

6. Based on Figure 6, draw I_X versus V_{IN}

(20 marks)

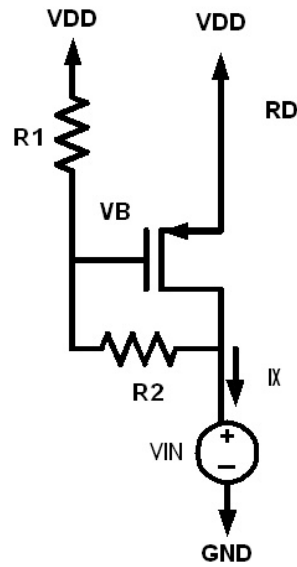


Figure 6

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